

1. [50 points]

For an NMOS transistor in the Ohmic region, with the bulk tied to the source, use the DC description

$$i_D = \frac{KP}{2} \frac{W}{L} [2(v_{GS} - V_{TO})v_{DS} - v_{DS}^2](1 + \lambda v_{DS})$$

- find analytic expressions for g_m and g_o
- using $KP=4 \cdot 10^{-5} \text{ A/V}^2$, $W=3L=10 \text{ microns}$, $V_{TO}=0.6 \text{ V}$, $\lambda=\text{lambda}=0.01/\text{V}$, evaluate i_D , g_m , and $r_o = 1/g_o$ at the bias point $V_{GS}=2 \text{ V}$, $V_{DS}=0.5 \text{ V}$
- draw the small signal equivalent circuit including the non-DC components
 $C_{gs}=3C_{gd}/2=3 \text{ pF}$.
- find the voltage transfer function, $V_{out}(s)/V_{in}(s)$ for an input applied to the gate (with respect to ground) and the output across a $10 \text{ K}\Omega$ load at the drain (with respect to ground).

2. [50 points]

Using 4007 MOS transistors design the following current mirrors to mirror an input current of 2 mA for a desired output current of 2 mA . In all cases give the Spice circuit and output current versus output voltage (that at the drain of the output transistor) for $9 \text{ V} \geq V_{out} \geq 0$. Discuss differences in the results and the amount of hardware needed.

- A basic current (sink) mirror of Figure 6.5, p. 563.
- A basic current (source) mirror as on the right of Figure 6.7, p. 566.
- The modified Wilson mirror of Figure 6.61(c).

3. [50 points]

For the npn BN2X4 transistors of the 2.0u technology MOSIS set:

- give Spice plots for i_C versus v_{CE} with i_B as a parameter with $5 \text{ V} \geq v_{CE} \geq 0$ for $9 \text{ uA} \geq i_B \geq 0$ in 3 uA steps.
- draw the small signal equivalent circuit for this transistor when biased at $I_C = 0.46 \text{ mA}$, $I_B = 6 \text{ uA}$. Also give the V_{CE} for this bias point and indicate the Q point on the Spice curves. .